# Power LDMOS transistor

AMPLEON Product data sheet

Rev. 3 — 29 August 2024

# 1. Product profile

### 1.1 General description

Based on Advanced Rugged Technology (ART), this 150 W LDMOS RF transistor has been designed to cover a wide range of applications for ISM, broadcast and communications. The unmatched transistor has a frequency range of 1 MHz to 650 MHz.

Table 1. Application information

Test signal	f	V <sub>DS</sub>	PL	Gp	η <sub>D</sub>
	(MHz)	(V)	(W)	(dB)	(%)
CW	64	65	150	32.1	78.8
CW	128	65	150	29.7	81.9

#### 1.2 Features and benefits

- High breakdown voltage enables class E operation up to V<sub>DS</sub> = 53 V
- Qualified up to a maximum of V<sub>DS</sub> = 65 V
- Characterized from 30 V to 65 V to support a wide range of applications
- Integrated dual sided ESD protection enables class C operation and complete switch off of the transistor
- Excellent ruggedness with no device degradation
- High efficiency
- Excellent thermal stability
- Designed for broadband operation
- For RoHS compliance see the product details on the Ampleon website

#### 1.3 Applications

- Industrial, scientific and medical applications
  - Plasma generators
  - MRI systems
  - ♦ CO₂ lasers
  - Particle accelerators
  - Defrosting
- Broadcast
  - FM radio
  - VHF TV
- Radar
  - Non cellular communications
  - UHF radar

# 2. Pinning information

Table 2. Pinning

Pin	Description	Description		Graphic symbol
1	drain			
2	gate		1	1 
3	source	[1]	2 3	2 - 3 3 sym112

<sup>[1]</sup> Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Package name	Orderable part number	12NC	<b>3 1</b>	Min. orderable quantity (pieces)
SOT467C	ART150FEU	9349 603 45112	Tray; 20-fold; non-dry pack	60

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	[1]	-	200	V
$V_{GS}$	gate-source voltage		-9	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[2]	-	225	°C

<sup>[1]</sup> Specified over lifetime at maximum operating temperature.

### 5. Thermal characteristics

Table 5. Thermal characteristics

According to standard MIL-STD-883E.

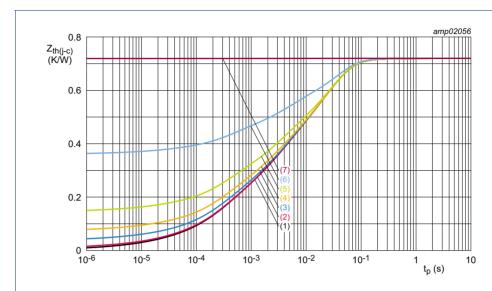
Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	T <sub>j</sub> = 125 °C, measured [1] under RF condition	0.72	K/W

<sup>[1]</sup> Refer to application note AN221014 on the Ampleon website.

[2] See Figure 1.

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator

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- (1)  $\delta$  = 0.1 % (single pulse)
- (2)  $\delta = 1 \%$
- (3)  $\delta = 5 \%$
- (4)  $\delta = 10 \%$
- (5)  $\delta = 20 \%$
- (6)  $\delta = 50 \%$
- (7)  $\delta = 100 \%$  (steady state)

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

# 6. Characteristics

Table 6. DC characteristics

 $T_i$  = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.11 \text{ mA}$	203	209	-	V
$V_{GS(th)}$	gate-source threshold voltage	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 111 mA	1.5	2.1	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 65 V	-	-	1.2	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 20 \text{ V}$	-	14.7	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 13 V; V <sub>DS</sub> = 0 V	-	-	120	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 3.885 \text{ A}$	_	0.482	-	Ω

Table 7. AC characteristics

 $T_i$  = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>rs</sub>	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 65 \text{ V}; f = 1 \text{ MHz}$	-	0.28	-	pF
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 65 V; f = 1 MHz	-	113	-	pF
C <sub>oss</sub>	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 65 \text{ V}; f = 1 \text{ MHz}$	-	34.4	-	pF

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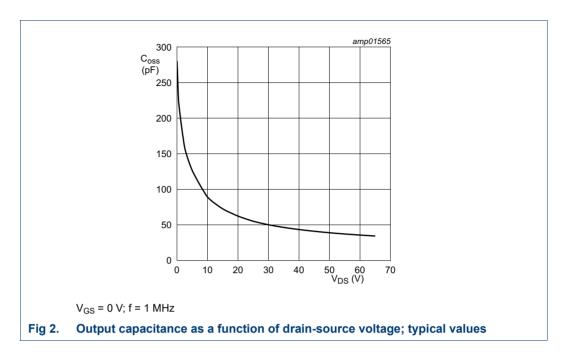


Table 8. RF characteristics

Test signal: CW pulsed;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %; f = 108 MHz; RF performance at  $V_{DS}$  = 65 V;  $I_{Dq}$  = 20 mA;  $T_{case}$  = 25 °C; unless otherwise specified; in a class-AB production test circuit.

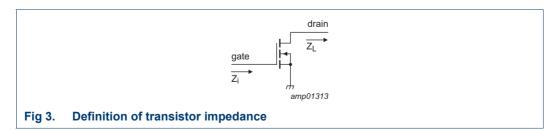
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L</sub> = 150 W	29	31	-	dB
RLin	input return loss	P <sub>L</sub> = 150 W	-	-14	-9	dB
$\eta_{D}$	drain efficiency	P <sub>L</sub> = 150 W	68	72	-	%

### 7. Test information

### 7.1 Ruggedness in class-AB operation

The ART150FE is capable of withstanding a load mismatch corresponding to VSWR  $\geq 65$ : 1 through all phases under the following conditions: V<sub>DS</sub> = 65 V; I<sub>Dq</sub> = 20 mA; P<sub>L</sub> = 150 W; f = 108 MHz; CW and CW pulsed (t<sub>p</sub> = 100  $\mu$ s;  $\delta$  = 10 %).

### 7.2 Impedance information



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Table 9. Typical impedance

Simulated  $Z_i$  and  $Z_L$  device impedance; impedance info at  $V_{DS}$  = 65 V and  $P_L$  = 150 W.

f	Z <sub>i</sub>	$Z_L$
(MHz)	<b>(Ω)</b>	<b>(Ω)</b>
108	5.5 – j23.0	12.1 + j4.8

### 7.3 Test circuit

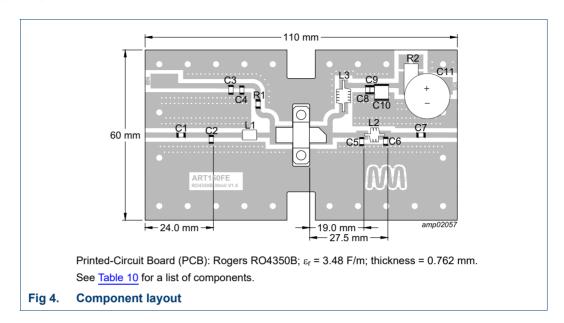


Table 10. List of components

For test circuit see Figure 4.

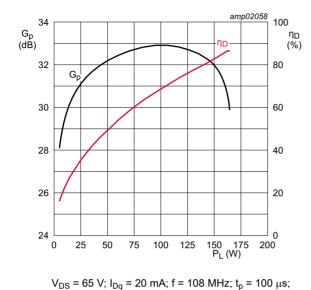
Component	Description	Value		Remarks
C1, C4, C7	multilayer ceramic chip capacitor	1 nF	[1][2]	
C2	multilayer ceramic chip capacitor	110 pF	[1][2]	
C3	multilayer ceramic chip capacitor	4.7 μF, 100 V		Murata: GRM31CC72A475KE11L
C5	multilayer ceramic chip capacitor	20 pF	[1][2]	
C6	multilayer ceramic chip capacitor	62 pF	[1][2]	
C8, C9	multilayer ceramic chip capacitor	620 pF	[1][2]	
C10	multilayer ceramic chip capacitor	4.7 μF, 100 V		TDK: CGA9N2X7R2A465K230
C11	electrolytic capacitor	470 μF, 100 V		
L1	midi spring air core inductor	39 nH		Coilcraft: 1812SMS-39N
L2	air core inductor	39 nH, 3 turns, D = 5 mm		1 mm copper wire
L3	air core inductor	82 nH, 5 turns, D = 5 mm		1 mm copper wire
R1	chip resistor	5.1 kΩ		SMD 1206
R2	chip resistor	0.01 Ω		FC4L110R010FER

<sup>[1]</sup> American Technical Ceramics type 800B or capacitor of same quality.

<sup>[2]</sup> Vertical mounted.

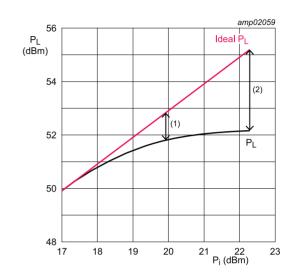
### 7.4 Graphical data

#### 7.4.1 CW pulsed



 $V_{DS}$  = 65 V;  $I_{Dq}$  = 20 mA; f = 108 MHz;  $t_p$  = 100 µs;  $\delta$  = 10 %.

Fig 5. Power gain and drain efficiency as function of output power; typical values

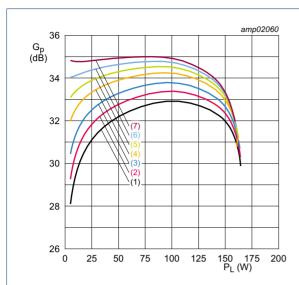


 $V_{DS}$  = 65 V;  $I_{Dq}$  = 20 mA; f = 108 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %.

- (1)  $P_{L(1dB)} = 51.79 \text{ dBm } (151 \text{ W})$
- (2)  $P_{L(3dB)} = 52.12 \text{ dBm } (164 \text{ W})$

Fig 6. Output power as a function of input power; typical values

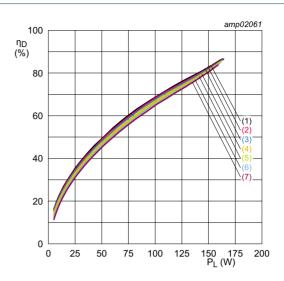
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 $V_{DS}$  = 65 V; f = 108 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %.

- (1)  $I_{Dq} = 20 \text{ mA}$
- (2)  $I_{Dq} = 50 \text{ mA}$
- (3)  $I_{Dq} = 100 \text{ mA}$
- (4)  $I_{Dq} = 200 \text{ mA}$
- (5)  $I_{Dq} = 300 \text{ mA}$
- (6)  $I_{Dq} = 400 \text{ mA}$
- (7)  $I_{Dq} = 500 \text{ mA}$

Fig 7. Power gain as a function of output power; typical values

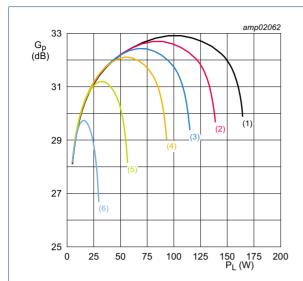


 $V_{DS}$  = 65 V; f = 108 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %.

- (1)  $I_{Dq} = 20 \text{ mA}$
- (2)  $I_{Dq} = 50 \text{ mA}$
- (3)  $I_{Dq} = 100 \text{ mA}$
- (4)  $I_{Dq} = 200 \text{ mA}$
- (5)  $I_{Dq} = 300 \text{ mA}$
- (6)  $I_{Dq} = 400 \text{ mA}$
- (7)  $I_{Dq} = 500 \text{ mA}$

Fig 8. Drain efficiency as a function of output power; typical values

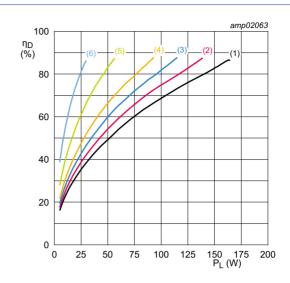
#### **Power LDMOS transistor**



 $I_{Dq}$  = 20 mA; f = 108 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %.

- (1)  $V_{DS} = 65 \text{ V}$
- (2)  $V_{DS} = 60 \text{ V}$
- (3)  $V_{DS} = 55 V$
- (4)  $V_{DS} = 50 \text{ V}$
- (5)  $V_{DS} = 40 \text{ V}$
- (6)  $V_{DS} = 30 \text{ V}$

Fig 9. Power gain as a function of output power; typical values



 $I_{Dq}$  = 20 mA; f = 108 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %.

- (1)  $V_{DS} = 65 \text{ V}$
- (2)  $V_{DS} = 60 \text{ V}$
- (3)  $V_{DS} = 55 V$
- (4)  $V_{DS} = 50 \text{ V}$
- (5)  $V_{DS} = 40 \text{ V}$
- (6)  $V_{DS} = 30 \text{ V}$

Fig 10. Drain efficiency as a function of output power; typical values

#### 7.4.2 CW

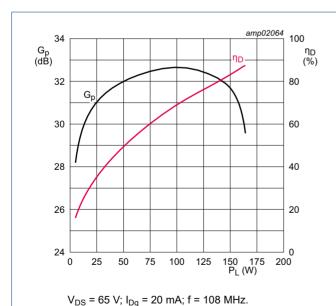
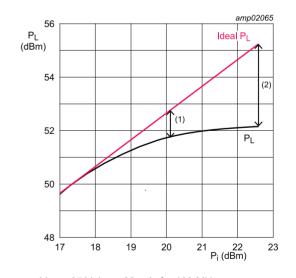


Fig 11. Power gain and drain efficiency as function of output power; typical values

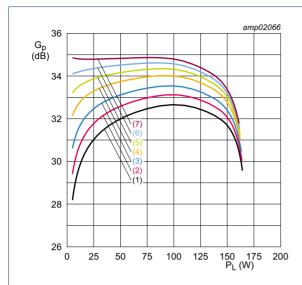


 $V_{DS} = 65 \text{ V}; I_{Dq} = 20 \text{ mA}; f = 108 \text{ MHz}.$ 

- (1)  $P_{L(1dB)} = 51.77 \text{ dBm } (150 \text{ W})$
- (2) P<sub>L(3dB)</sub> = 52.15 dBm (164 W)

Fig 12. Output power as a function of input power; typical values

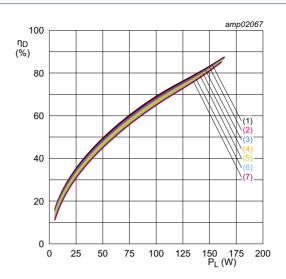
#### **Power LDMOS transistor**



 $V_{DS} = 65 \text{ V}; f = 108 \text{ MHz}.$ 

- (1)  $I_{Dq} = 20 \text{ mA}$
- (2)  $I_{Dq} = 50 \text{ mA}$
- (3)  $I_{Dq} = 100 \text{ mA}$
- (4)  $I_{Dq} = 200 \text{ mA}$
- (5)  $I_{Dq} = 300 \text{ mA}$
- (6)  $I_{Dq} = 400 \text{ mA}$
- (7)  $I_{Dq} = 500 \text{ mA}$

Fig 13. Power gain as a function of output power; typical values

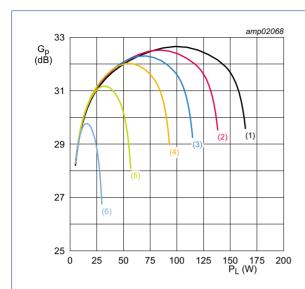


 $V_{DS} = 65 \text{ V}; f = 108 \text{ MHz}.$ 

- (1)  $I_{Dq} = 20 \text{ mA}$
- (2)  $I_{Dq} = 50 \text{ mA}$
- (3)  $I_{Dq} = 100 \text{ mA}$
- (4)  $I_{Dq} = 200 \text{ mA}$
- (5)  $I_{Dq} = 300 \text{ mA}$
- (6)  $I_{Dq} = 400 \text{ mA}$
- (7)  $I_{Dq} = 500 \text{ mA}$

Fig 14. Drain efficiency as a function of output power; typical values

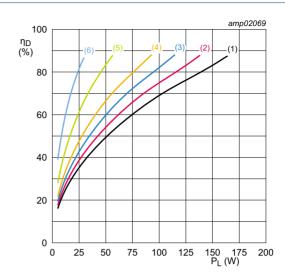
#### **Power LDMOS transistor**



 $I_{Dq} = 20 \text{ mA}$ ; f = 108 MHz.

- (1)  $V_{DS} = 65 \text{ V}$
- (2)  $V_{DS} = 60 \text{ V}$
- (3)  $V_{DS} = 55 V$
- (4)  $V_{DS} = 50 \text{ V}$
- (5)  $V_{DS} = 40 \text{ V}$
- (6)  $V_{DS} = 30 \text{ V}$

Fig 15. Power gain as a function of output power; typical values



 $I_{Dq} = 20 \text{ mA}$ ; f = 108 MHz.

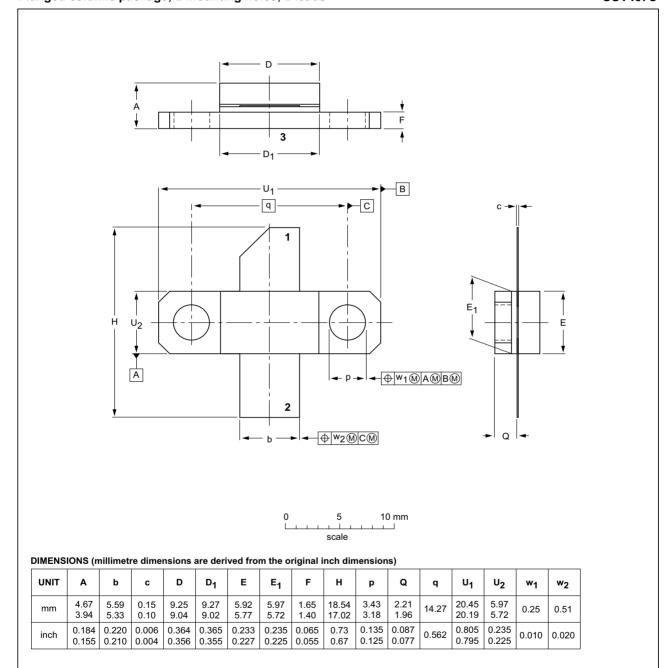
- (1)  $V_{DS} = 65 V$
- (2)  $V_{DS} = 60 \text{ V}$
- (3)  $V_{DS} = 55 V$
- (4)  $V_{DS} = 50 \text{ V}$
- (5)  $V_{DS} = 40 \text{ V}$
- (6)  $V_{DS} = 30 \text{ V}$

Fig 16. Drain efficiency as a function of output power; typical values

# 8. Package outline

#### Flanged ceramic package; 2 mounting holes; 2 leads

SOT467C



OUTLINE		REFERENCES				
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT467C						<del>99-12-28</del> 12-05-02

Fig 17. Package outline SOT467C

**Power LDMOS transistor** 

# 9. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2

## 10. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
FM	Frequency Modulation
ISM	Industrial, Scientific and Medical
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MRI	Magnetic Resonance Imaging
MTF	Median Time to Failure
RoHS	Restriction of Hazardous Substances
UHF	Ultra High Frequency
VHF	Very High Frequency
VSWR	Voltage Standing Wave Ratio

# 11. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
ART150FE v.3	20240829	Product data sheet	-	ART150FE v.2	
Modifications:	<ul> <li>Table 1 on page 1: table updated</li> <li>Section 5 on page 2: updated section</li> <li>Section 7 on page 4: updated section</li> </ul>				
ART150FE v.2	20220708	Product data sheet	-	ART150FE v.1	
ART150FE v.1	20210104	Product data sheet	-	-	

#### **Power LDMOS transistor**

# 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="https://www.ampleon.com">https://www.ampleon.com</a>.

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For sales office addresses, please visit: http://www.ampleon.com/sales

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# ART150FE

#### **Power LDMOS transistor**

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